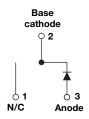


# HEXFRED®, Ultrafast Soft Recovery Diode, 8 A



TO-263AB (D<sup>2</sup>PAK)



PRODUCT SUMMARY								
Package	TO-263AB (D <sup>2</sup> PAK)							
I <sub>F(AV)</sub>	8 A							
$V_{R}$	1200 V							
V <sub>F</sub> at I <sub>F</sub>	2.4 V							
t <sub>rr</sub> (typ.)	28 ns							
T <sub>J</sub> max.	150 °C							
Diode variation	Single die							

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA08TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V <sub>R</sub>		1200	V					
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8						
Single pulse forward current	I <sub>FSM</sub>		130	Α					
Maximum repetitive forward current	I <sub>FRM</sub>		32						
Maximum nawar dissination	В	T <sub>C</sub> = 25 °C	73.5	- w					
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 100 °C	29						
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C					





<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V <sub>BR</sub>	Ι <sub>R</sub> = 100 μΑ	1200	-	-				
Maximum forward voltage		I <sub>F</sub> = 8.0 A	-	2.6	3.3	V			
	V <sub>FM</sub>	I <sub>F</sub> = 16 A	-	3.4	4.3				
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125 °C	-	2.4	3.1				
Maximum reverse		$V_R = V_R$ rated	-	0.31	10				
leakage current	I <sub>RM</sub>	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	-	135	1000	μΑ			
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	11	20	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V <sub>R</sub> = 30 V	-	28	-	ns		
	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	63	95			
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	106	160			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.5	8.0	- A		
	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/µs}$	-	6.2	11			
Povorco rocovony oborgo	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	140	380			
Reverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	335	880	110		
Peak rate of fall of recovery current during t <sub>b</sub>	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	133	1	- A/μs		
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	85	-			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.7	K/W			
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	40	N/VV			
Weight			-	2.0	-	g			
vveigitt			-	0.07	-	oz.			
Marking device		Case style TO-263AB (D <sup>2</sup> PAK)		HFA08	TB120S				

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## Vishay Semiconductors

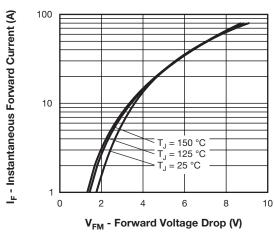


Fig. 1 - Maximum Forward Voltage Drop Characteristics

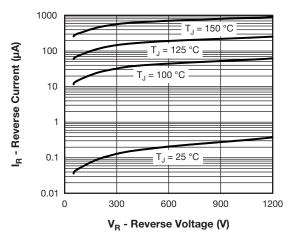


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

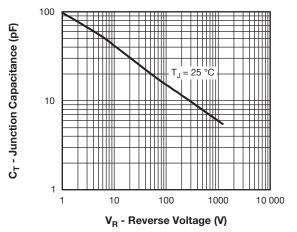


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

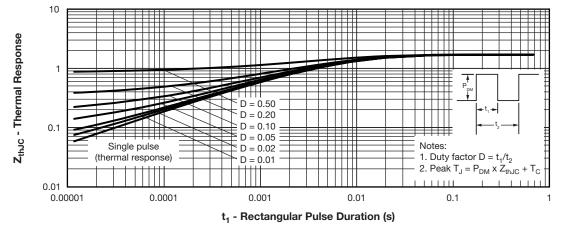


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics





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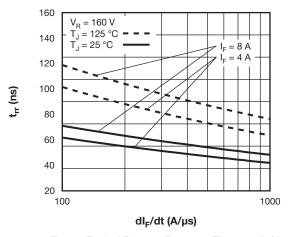


Fig. 5 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

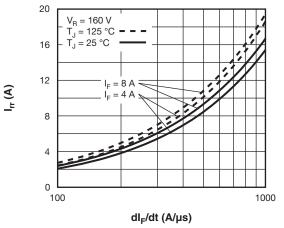


Fig. 6 - Typical Recovery Current vs. dI<sub>F</sub>/dt

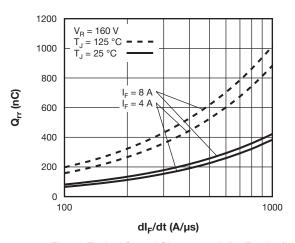


Fig. 7 - Typical Stored Charge vs. dI<sub>F</sub>/dt (Per Leg)

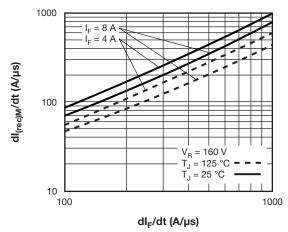


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 

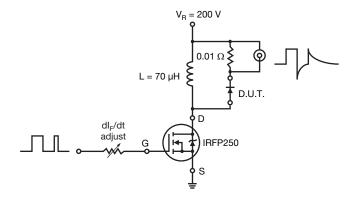
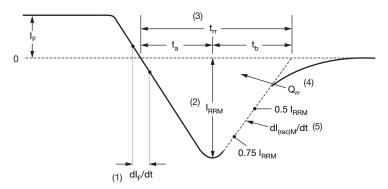


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

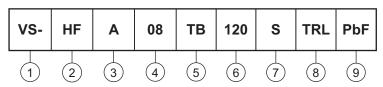
(5) dI<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions



#### **ORDERING INFORMATION TABLE**

### Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

- Process designator: A = electron irradiated

4 - Current rating (08 = 8 A)

Package outline (TB = TO-220, 2 leads)

Voltage rating (120 = 1200 V)

7 -  $S = D^2PAK$ 

8 - • None = tube

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

PbF = lead (Pb)-free, for tube packaged

• P = lead (Pb)-free, for tape and reel packaged

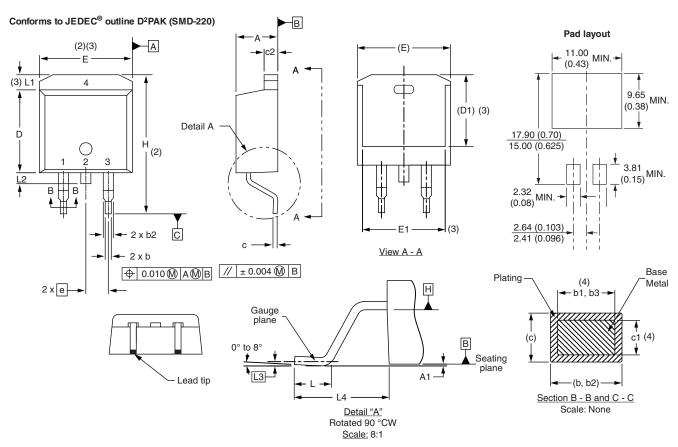
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA08TB120SPBF	50	1000	Antistatic plastic tube						
VS-HFA08TB120STRRP	800	800	13" diameter reel						
VS-HFA08TB120STRLP	800	800	13" diameter reel						



## D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	2.54 BSC 0.100 BSC			
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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